

Product data sheet

1. General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low forward voltage drop
- Low thermal resistance
- Soft recovery characteristic

3. Applications

- High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 71 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	10	A
Static charact	eristics	·				
V _F	forward voltage	I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	-	1.6	V
Dynamic char	acteristics					_
t _{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T _j = 25 °C; <u>Fig. 7</u>	-	20	-	ns





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K A
2	А	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering information								
Type number	Package	age						
	Name	Description	Version					
BYV10X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113					

7. Marking

Table 4. Marking codes	
Type number	Marking code
BYV10X-600P	BYV10X-600P

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 71 °C; square-wave pulse; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	10	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; T_h ≤ 71 °C; square-wave pulse	-	20	A
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Symbol	Parameter	Conditions	Min	Мах	Unit
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	80	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	88	A
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

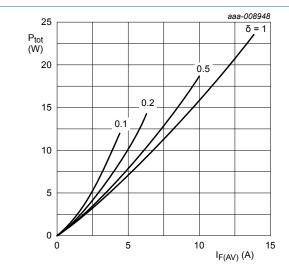
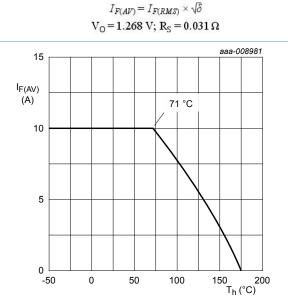


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values





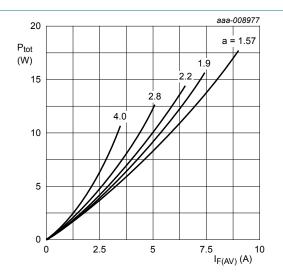
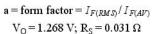


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



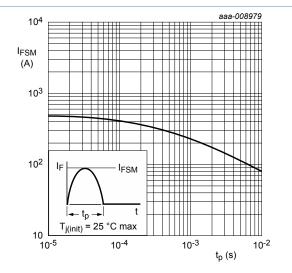


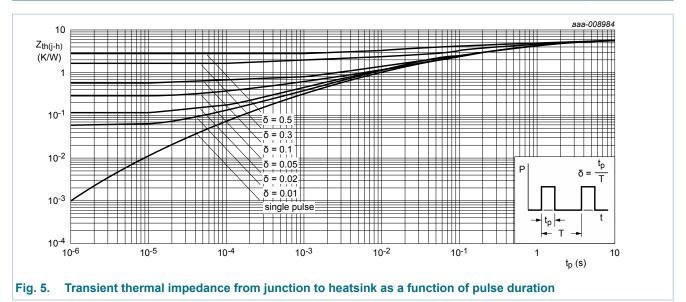
Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. 1	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance	without heatsink compound	-	-	7.2	K/W
	from junction to heatsink	with heatsink compound ; Fig. 5	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



10. Isolation characteristics

Table 7. Isolation characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz ; from cathode to external heatsink		-	10	-	pF

11. Characteristics

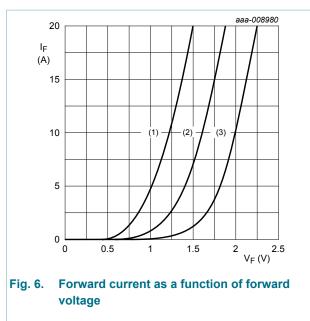
Table 8. Characteristics									
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit		
Static chara	Static characteristics								
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.5	2	V		
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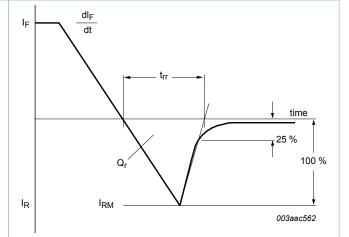
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	-	1.6	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 500 V; T _j = 150 °C	-	-	250	μA
Dynamic cha	aracteristics					,
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	35	50	ns
		I_F = 1 A; V _R = 30 V; dI _F /dt = 100 A/µs; T _j = 25 °C; <u>Fig. 7</u>	-	20	-	ns
		I _F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	40	-	ns



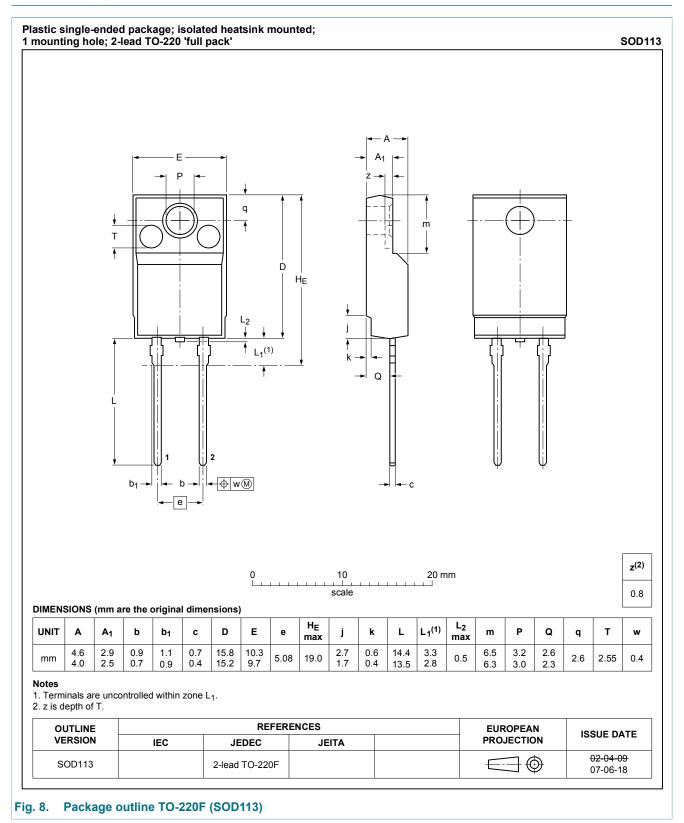
(1) $T_j = 150$ °C; typical values; (2) $T_j = 150$ °C; maximum values; (3) $T_j = 25$ °C; maximum values; $V_0 = 1.268$ V; $R_S = 0.031 \Omega$





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12. Package outline



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13. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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